PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1 Stylesheet Version v1.2

Version v1.1 EPAS ID: PAT6657489

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date
Yung-Fong Lin	03/31/2021
Yu-Chieh Chou	03/31/2021
Tsung-Hsiang Lin	03/31/2021
Li-Wen Chuang	04/07/2021

RECEIVING PARTY DATA

Name:	Vanguard International Semiconductor Corporation
Street Address:	123, Park Ave-3rd, Hsinchu Science Park
City:	Hsinchu
State/Country:	TAIWAN

PROPERTY NUMBERS Total: 1

Property Type	Number
Application Number:	17231032

CORRESPONDENCE DATA

Fax Number:

Correspondence will be sent to the e-mail address first; if that is unsuccessful, it will be sent using a fax number, if provided; if that is unsuccessful, it will be sent via US Mail.

Phone: 3027291562

Email: Patent.admin.uspto.cr@naipo.com

Correspondent Name: WINSTON HSU

Address Line 1: 5F., NO.389, FUHE RD., YONGHE DIST.,

Address Line 4: NEW TAIPEI CITY, TAIWAN

ATTORNEY DOCKET NUMBER:	VISP0060USA
NAME OF SUBMITTER:	KATE YEH
SIGNATURE:	/KATE YEH/
DATE SIGNED:	04/15/2021

Total Attachments: 8

source=4181435#page1.tif

source=4181435#page2.tif

source=4181435#page3.tif

source=4181435#page4.tif

PATENT REEL: 055923 FRAME: 0827

506610682



PATENT REEL: 055923 FRAME: 0828

Title of Invention: HIGH ELECTRON MOBILITY TRANSISTOR AND FABRICATION METHOD THEREOF

As the below named inventor, I here this declaration is directed to:	by declare that:		
☑ The attached application, or			
☐ United States application nut	mber	filed on,	or
☐ PCT international application	number	filed on	
The above-identified application was	made or authorized to be made by	y me.	
I believe that I am the original invente application.	or or an original joint inventor of a	claimed invention in the	
I hereby acknowledge that any willful under18 U.S.C. 1001 by fine or impri			
In consideration of the payment by	Vanguard International Semiconductor Corporation	having a postal addr	ess of
123, Park Ave-3rd, Hsinchu Sc	cience Park, Hsinchu 30077,	Taiwan, R.O.C.	
(referred to as "ASSIGNEE" below) to acknowledged, and for other good an	ol of the sum of One Dollar (\$ 1.00 d valuable consideration.), the receipt of which is here	eby
I hereby sell, assign and transfer to ASSIGNEE and the successors and assignees of the ASSIGNEE the entire right, title and interest in and to any and all improvements which are disclosed in the invention as above-identified application and, in and to, all Letters Patent to be obtained for said invention by the above application or any continuations, continuation-in-part, divisions, renewals, substitutes, or extensions thereof, and as to Letters Patent any reissue or re-examination thereof.			
I hereby covenant that no assignment, sale, agreement or encumbrance has been or will be made or entered into which would conflict with this assignment;			
I further covenant that ASSIGNEE will, upon its request, be provided promptly with all pertinent facts and documents relating to said invention and said Letters Patent and legal equivalents as may be known and accessible to I and will testify as to the same in any interference, litigation proceeding related thereto and will promptly execute and deliver to ASSIGNEE or its legal			
representatives any and all papers, is maintain, issue and enforce said app equivalents thereof which may be ne IN WITNESS WHEREOF, I have her	lication, said invention and said Le cessary or desirable to carry out the	etters Patent and said ne proposes thereof.	
Note: An application data sheet (PTC inventive entity, must accompany this	D/SB/14 or equivalent), including no s form. Use this form for <u>each addi</u>	aming the entire tional inventor.	

Page 1 of 8

NPO#VIS-P0060-USA:0 CUST#109039

LEGAL NA	ME OF INVENTOR(ASSIGNOR)		
Inventor:	Yung-Fong Lin	Date:	03/7//20=1
Signature:	Yung- Kong L	·îh:	
	0 ()		

Page 2 of 8

Title of Invention: HIGH ELECTRON MOBILITY TRANSISTOR AND FABRICATION METHOD THEREOF

As the below named inventor, I here This declaration is directed to:	by declare that:		
☑ The attached application, or			
☐ United States application nu	mber	filed on,	or
☐ PCT international application	number	filed on	
The above-identified application was	made or authorized to be made t	by me.	
I believe that I am the original invent application.	or or an original joint inventor of a	claimed invention in the	
I hereby acknowledge that any willfu under18 U.S.C. 1001 by fine or impri			
In consideration of the payment by	Vanguard International Semiconductor Corporatio	having a postal addi	ress of
123, Park Ave-3rd, Hsinchu S	cience Park, Hsinchu 30077	′, Taiwan, R.O.C.	
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good an	o I of the sum of One Dollar (\$ 1.0 and valuable consideration.	0), the receipt of which is her	eby
I hereby sell, assign and transfer to a the entire right, title and interest in an invention as above-identified applica- invention by the above application of substitutes, or extensions thereof, an	nd to any and all improvements w tion and, in and to, all Letters Pat rany continuations, continuation-i	hich are disclosed in the ent to be obtained for said n-part, divisions, renewals,	EE
I hereby covenant that no assignment entered into which would conflict with		ce has been or will be made	or
I further covenant that ASSIGNEE will, upon its request, be provided promptly with all pertinent facts and documents relating to said invention and said Letters Patent and legal equivalents as may be known and accessible to I and will testify as to the same in any interference, litigation proceeding related thereto and will promptly execute and deliver to ASSIGNEE or its legal			
representatives any and all papers, i maintain, issue and enforce said app equivalents thereof which may be no IN WITNESS WHEREOF, I have he	plication, said invention and said Lacessary or desirable to carry out	etters Patent and said the proposes thereof.	
Note: An application data sheet (PTC inventive entity, must accompany thi			

Page 3 of 8

NPO#VIS-P0060-USA:0 CUST#109039

LEGAL NAME OF INVENTOR(ASSIGNOR)

inventor:

Yu-Chieh Chou

Date:

 $\frac{3}{31}$

Signature:

Page 4 of 8

Title of Invention:

HIGH ELECTRON MOBILITY TRANSISTOR AND FABRICATION METHOD THEREOF

As the below named inventor, I herel This declaration is directed to:	by declare that:		
☑ The attached application, or			
☐ United States application nu	mber	filed on	, or
☐ PCT international application	number	filed on	•
The above-identified application was	made or authorized to be made b	y me.	
I believe that I am the original inventor application.	or or an original joint inventor of a	claimed invention in the	
I hereby acknowledge that any willful under18 U.S.C. 1001 by fine or impri	false statement made in this dec sonment of not more than five (5)	aration is punishable years, or both.	
	Vanguard International Semiconductor Corporatio	having a postal a	address of
123, Park Ave-3rd, Hsinchu Sc	cience Park, Hsinchu 30077	, Taiwan, R.O.C.	
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good an	l of the sum of One Dollar (\$ 1.00 d valuable consideration.)), the receipt of which is	hereby
I hereby sell, assign and transfer to ASSIGNEE and the successors and assignees of the ASSIGNEE the entire right, title and interest in and to any and all improvements which are disclosed in the invention as above-identified application and, in and to, all Letters Patent to be obtained for said invention by the above application or any continuations, continuation-in-part, divisions, renewals, substitutes, or extensions thereof, and as to Letters Patent any reissue or re-examination thereof.			
I hereby covenant that no assignment, sale, agreement or encumbrance has been or will be made or entered into which would conflict with this assignment;			
I further covenant that ASSIGNEE will, upon its request, be provided promptly with all pertinent facts and documents relating to said invention and said Letters Patent and legal equivalents as may be known and accessible to I and will testify as to the same in any interference, litigation proceeding related thereto and will promptly execute and deliver to ASSIGNEE or its legal			
representatives any and ail papers, ir maintain, issue and enforce said app equivalents thereof which may be ne IN WITNESS WHEREOF, I have her	lication, said invention and said L cessary or desirable to carry out t	etters Patent and said he proposes thereof.	
Note: An application data sheet (PTC inventive entity, must accompany this	0/SB/14 or equivalent), including r s form. Use this form for <u>each add</u>	aming the entire itional inventor.	

Page 5 of 8

NPO#VIS-P0060-USA:0 CUST#109039

LEGAL NAME OF INVENTOR(ASSIGNOR)

Inventor: Tsung-Hsiang Lin

Date: 202), 3, 3

signature: Tswny-Hsiang Lin

Page 6 of 8

Title of Invention: HIGH ELECTRON MOBILITY TRANSISTOR AND FABRICATION METHOD THEREOF

As the below named inventor, I here This declaration is directed to:	by declare that:		
☑ The attached application, or			
☐ United States application number		filed on	, or
☐ PCT international application	number	filed on	
The above-identified application was	made or authorized to be made t	y me.	
I believe that I am the original invent application.	or or an original joint inventor of a	claimed invention in the	
I hereby acknowledge that any willfu under18 U.S.C. 1001 by fine or impr	l false statement made in this dec isonment of not more than five (5)	aration is punishable years, or both.	
In consideration of the payment by	Vanguard International Semiconductor Corporatio	having a postal addi	ress of
123, Park Ave-3rd, Hsinchu S	cience Park, Hsinchu 30077	, Taiwan, R.O.C.	
(referred to as "ASSIGNEE"below) to acknowledged, andfor other good an	o I of the sum of One Dollar (\$ 1.0) d valuable consideration.	3), the receipt of which is her	reby
I hereby sell, assign and transfer to ASSIGNEE and the successors and assignees of the ASSIGNEE the entire right, title and interest in and to any and all improvements which are disclosed in the invention as above-identified application and, in and to, all Letters Patent to be obtained for said invention by the above application or any continuations, continuation-in-part, divisions, renewals, substitutes, or extensions thereof, and as to Letters Patent any reissue or re-examination thereof.			
I hereby covenant that no assignmer entered into which would conflict with	nt, sale, agreement or encumbrand n this assignment;	e has been or will be made	or
I further covenant that ASSIGNEE wand documents relating to said inver known and accessible to I and will te related thereto and will promptly exe	ition and said Letters Patent and li stify as to the same in any interfer	egal equivalents as may be ence, litigation proceeding	ts
representatives any and all papers, i maintain, issue and enforce said app equivalents thereof which may be ne IN WITNESS WHEREOF, I have her	dication, said invention and said L cessary or desirable to carry out t	etters Patent and said he proposes thereof.	
Note: An application data sheet (PTC inventive entity, must accompany thi	D/SB/14 or equivalent), including r s form. Use this form for <u>each add</u>	aming the entire itional inventor.	

Page 7 of 8

NPO#VIS-P0060-USA:0 CUST#109039

LEGAL NA	ME OF INVENTOR(ASS	signor)			
Inventor:	Li-Wen Chuang		Date:	04/07/2021	
Signature:	Li-Wen	Chang			

Page 8 of 8

NPO#VIS-P0060-USA:0

F#NPO-P0002E-US1201 DSB0-110U010069

PATENT REEL: 055923 FRAME: 0836

RECORDED: 04/15/2021